

Laser processing of SiC: From graphene-coated SiC particles to 3D graphene froths

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Motivation

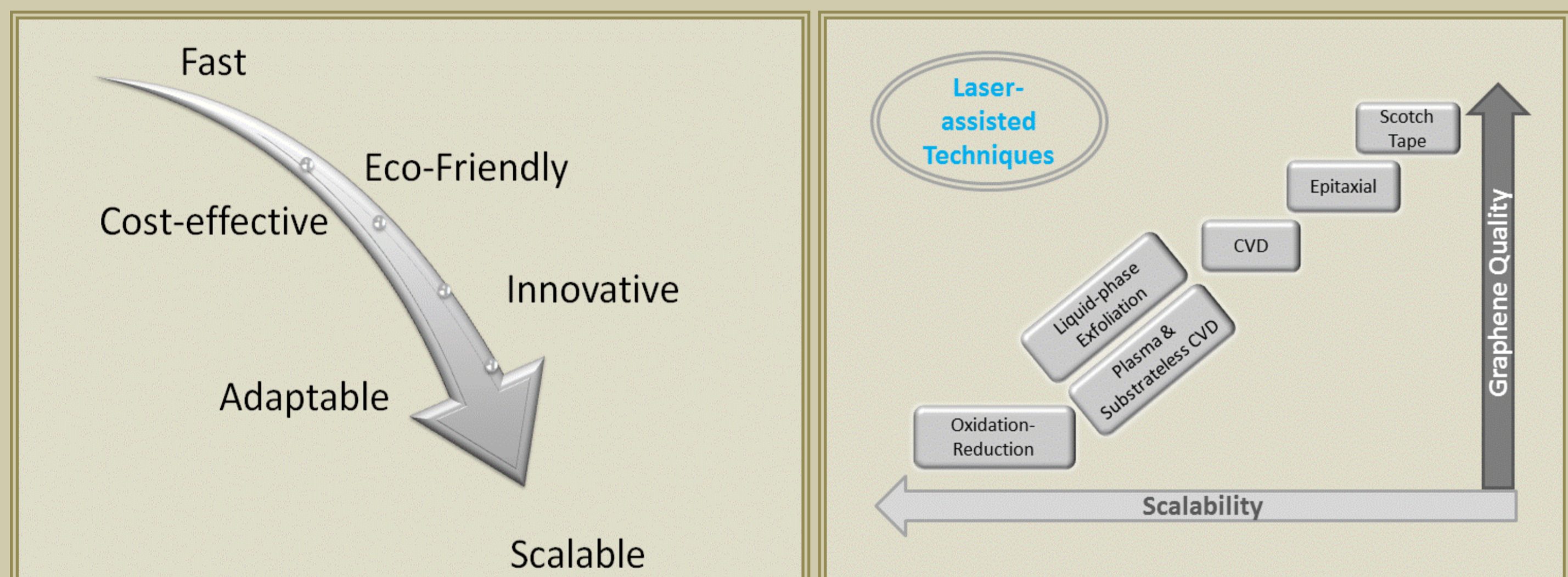
- We explore the feasibility of laser-assisted graphitization of micron sized SiC particles.
- It is demonstrated that laser-mediated SiC decomposition, at nearly ambient conditions, can result in a manifold of graphene structures e.g. SiC particles covered by few-layer epitaxial graphene up to highly porous graphene-like structures (froth morphology).
- SiC particles coated by few-layer graphene films are considered for applications in macro- and nano-electromechanical systems owing to their very high electrical conductivity.
- The enhanced mechanical properties of graphene-coated SiC particles may be suitable for body armor applications.

Introduction

Laser-Assisted Graphene Growth and Processing

Graphene Growth	Graphene Processing
<ul style="list-style-type: none"> Epitaxial on SiC Ablation of Graphite Decomposition of Organic Films Laser Exfoliation in Liquids Heat source for CVD growth 	<ul style="list-style-type: none"> GO Reduction to Graphene Laser Thinning of Multilayer Graphene

Advantages of Lasers in Graphene production



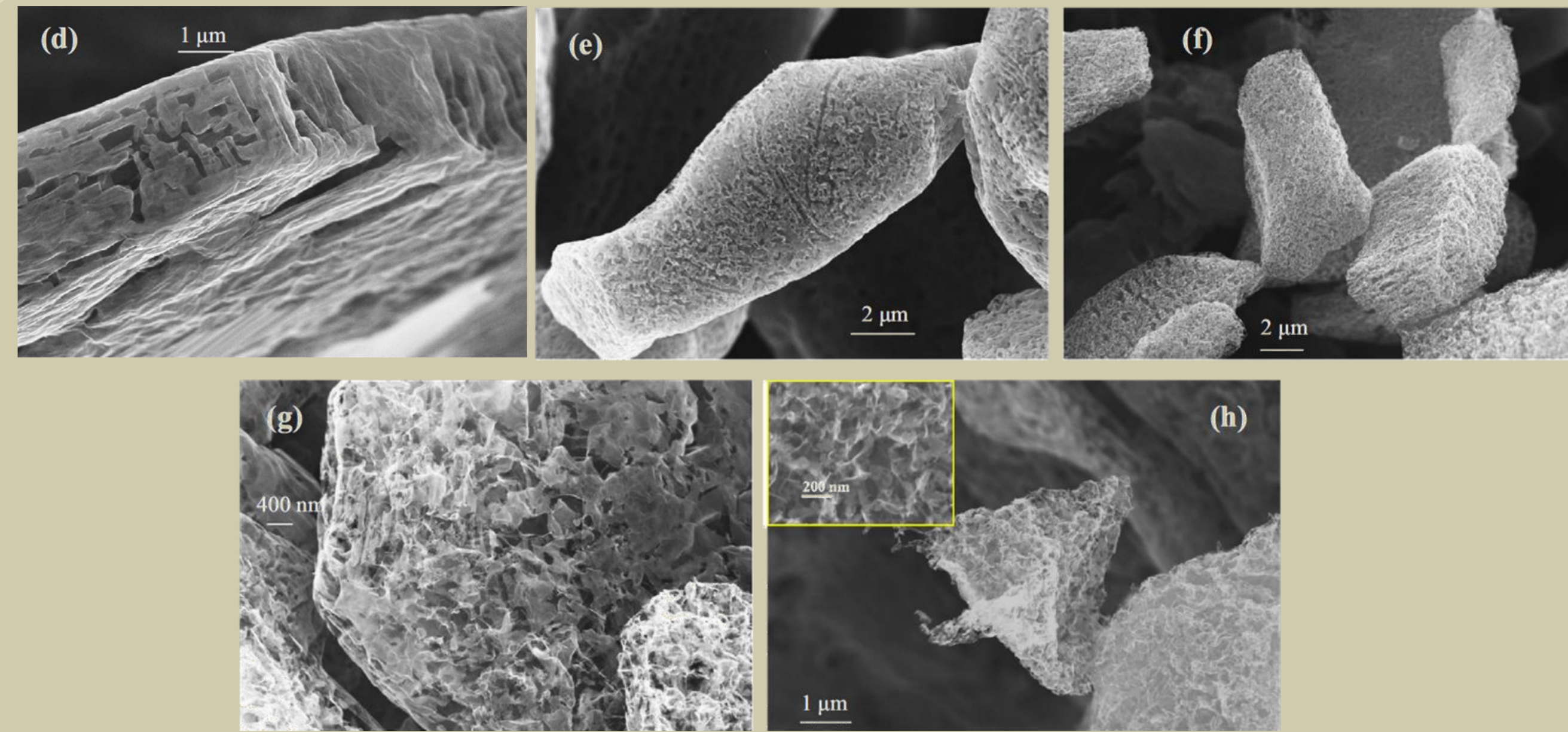
Experimental

- ✓ α -SiC powders: average particles sizes 2 μm and 20 μm .
- ✓ Laser irradiation took place using a CO₂ laser (10.6 μm) with power levels between 15 and 30% of the maximum power (240 W)
- ✓ Irradiation duration: few seconds
- ✓ Graphitization process at almost ambient conditions (mild flow of shielding Ar gas)

Results

Graphitization of 20 μm SiC particles

Field Emission Scanning Electron Microscopy



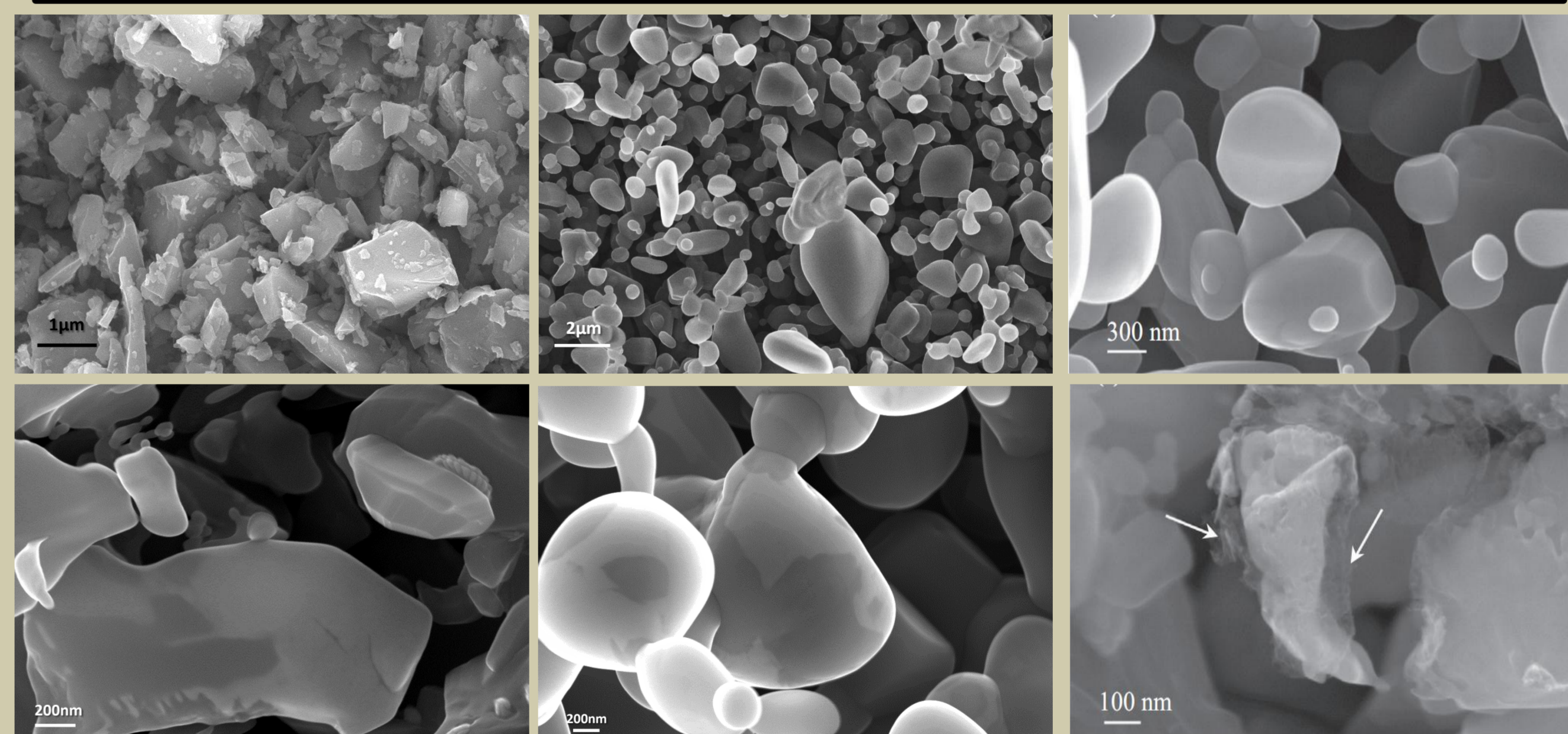
Typical FE-SEM images of laser-processed SiC particles (20 μm). From (a) to (h) images correspond to structures subjected to progressively higher dose.

HRTEM and Raman Spectroscopy studies

Representative Stokes-side Raman spectra of laser processed SiC particles (20 μm). The 2D band of spectrum (d) has been fitted by a single Lorentzian line shown by the solid line passing through the data points. The Raman spectra, from (a) to (f), roughly correspond to specimen regions from where the FE-SEM images 2(b) to (g) were recorded.

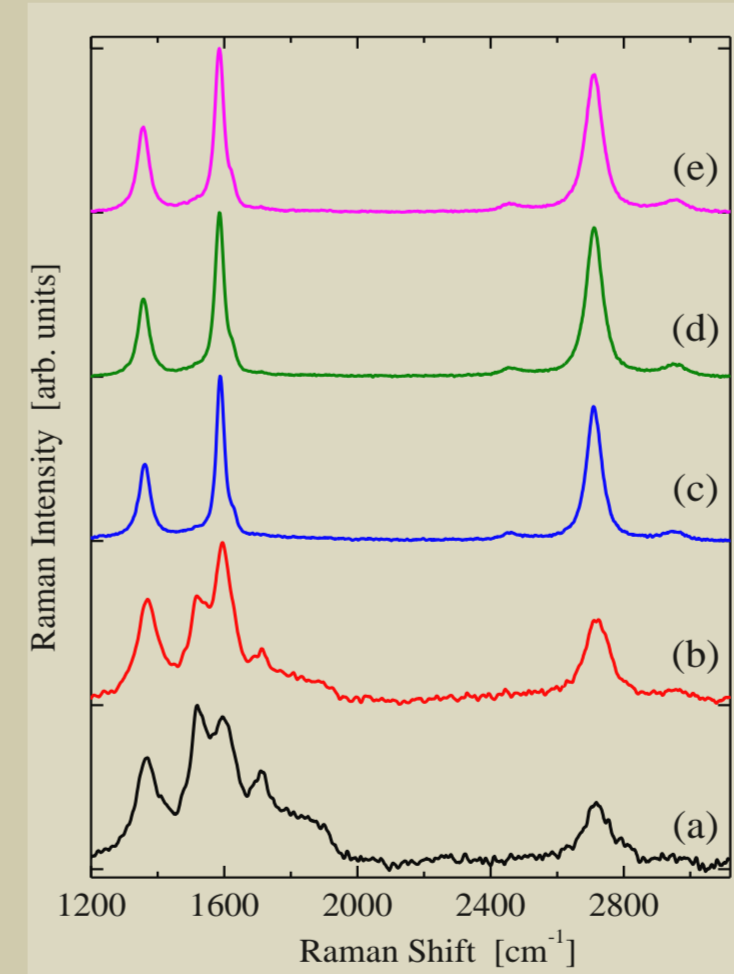
Graphitization of 2 μm SiC particles

Field Emission Scanning Electron Microscopy



Typical FE-SEM images of laser-processed SiC particles (2 μm)

Raman Spectroscopy study



- ✓ Representative Stokes-side Raman spectra of laser processed SiC particles (2 μm). Their intensities have been normalized to unity (for the more intense band) and their baselines have been off-set for clarity.
- ✓ In all cases, the single Lorentzian line-shape of the 2D band, reveals the growth of graphene-like films.

More details can be found in:
 A. Antonelou, V. Dracopoulos and S. N. Yannopoulos, Carbon 85, 176–184 (2015).

Concluding Remarks

- The results presented here demonstrate that depending on the SiC particle size and irradiation details, graphitization can take place under various morphologies
- Laser-induced graphitization is evidently a versatile and adaptable technique for the preparation of carbide-derived carbons from inorganic precursors
- Scalability of laser-assisted graphitized SiC particles production to large scale appears realistic in view of the high rate of laser processing (short time decomposition)